



NPN PRE-BIASED SMALL SIGNAL DUAL SURFACE MOUNT TRANSISTOR

Features

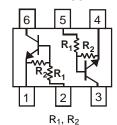
- Epitaxial Planar Die Construction
- Complementary PNP Types Available (DDA)
- Built-In Biasing Resistors
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

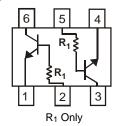
P/N	R1	R2	MARKING
DDC124EH	22ΚΩ	22ΚΩ	N17
DDC144EH	47ΚΩ	47ΚΩ	N20
DDC143EH	4.7ΚΩ	4.7ΚΩ	N08
DDC114YH	10ΚΩ	47ΚΩ	N14
DDC123JH	2.2ΚΩ	47ΚΩ	N06
DDC114EH	10ΚΩ	10ΚΩ	N13
DDC143TH	4.7ΚΩ	_	N07
DDC114TH	10ΚΩ	_	N12

Mechanical Data

- Case: SOT-563
- Case Material: Molded Plastic; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (23)
- Terminal Connections: See Diagram
- Weight: 0.005 grams (Approximate)

SCHEMATIC DIAGRAM, TOP VIEW





Ordering Information (Note 4)

Device	Packaging	Shipping
DDC124EH-7	SOT-563	3,000/Tape & Reel
DDC144EH-7	SOT-563	3,000/Tape & Reel
DDC143EH-7	SOT-563	3,000/Tape & Reel
DDC114YH-7	SOT-563	3,000/Tape & Reel
DDC123JH-7	SOT-563	3,000/Tape & Reel
DDC114EH-7	SOT-563	3,000/Tape & Reel
DDC143TH-7	SOT-563	3,000/Tape & Reel
DDC114TH-7	SOT-563	3,000/Tape & Reel

- Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 - 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

SOT-563

NXXYM

Nxx = Product Type Marking Code YM = Date Code Marking

Y = Year ex: T = 2006 M = Month ex: 9 = September

Date Code Key

Year	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	Р	R	S	T	U	V	W	Χ	Υ	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Supply Voltage		Vcc	50	V
Input Voltage	DDC124EH DDC144EH DDC143EH DDC114YH DDC123JH DDC114EH DDC143TH DDC114TH	V _{IN}	-10 to +40 -10 to +40 -10 to +30 -6 to +40 -5 to +12 -10 to +40 -5V max -5V max	V
Output Current	DDC124EH DDC144EH DDC143EH DDC114YH DDC123JH DDC114EH DDC143TH DDC114TH	lo	30 30 100 70 100 50 100	mA
Output Current	All	I _C (Max)	100	mA
Power Dissipation		P_d	150	mW
Thermal Resistance, Junction to Ambient Air	(Note 5)	$R_{ hetaJA}$	833	°C/W
Operating and Storage Temperature Range		T _j , T _{STG}	-55 to +150	°C

Note: 5. Mounted on FR4 Board with recommended pad layout at http://www.diodes.com/datasheets/ap02001.pdf.



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

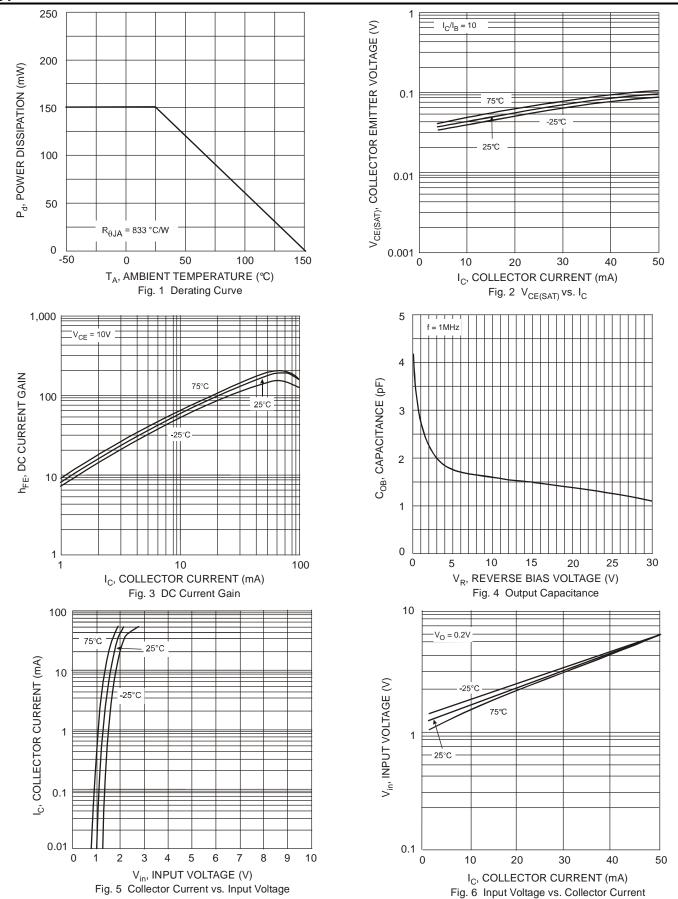
Characteristic (DDC143TH & DDC114TH only)	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_CBO	50	_	_	٧	I _C = 50μA
Collector-Emitter Breakdown Voltage	BV _{CEO}	50	_	_	٧	I _C = 1mA
Emitter-Base Breakdown Voltage	BV _{EBO}	5	_	_	V	I _E = 50μA
Collector Cut-Off Current	I _{CBO}	_	_	0.5	μΑ	V _{CB} = 50V
Emitter Cut-Off Current	I _{EBO}	_	_	0.5	μΑ	V _{EB} = 4V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	1	_	0.3	V	$I_C/I_B = 2.5 \text{mA} / 0.25 \text{mA}$ DDC143TH $I_C/I_B = 1 \text{mA} / 0.1 \text{mA}$ DDC114TH
DC Current Transfer Ratio	h _{FE}	100	250	600	_	$I_C = 1$ mA, $V_{CE} = 5$ V
Gain-Bandwidth Product*	f⊤	_	250	_	MHz	V _{CE} = 10V, I _E = -5mA, f = 100MHz

Characterist	tic	Symbol	Min	Тур	Max	Unit	Test Condition
	DDC124EH DDC144EH DDC143EH DDC114YH DDC123JH DDC114EH	VI(off)	0.5 0.5 0.5 0.3 0.5 0.5	1.1 1.1 1.1 — — 1.1			V _{CC} = 5V, I _O = 100μA
Input Voltage	DDC124EH DDC144EH DDC143EH DDC114YH DDC123JH DDC114EH	V _{I(on)}		1.9 1.9 1.9 — — 1.9	3.0 3.0 3.0 1.4 1.1 3.0	V	$V_{O} = 0.3V$, $I_{O} = 5mA$ $V_{O} = 0.3V$, $I_{O} = 2mA$ $V_{O} = 0.3V$, $I_{O} = 20mA$ $V_{O} = 0.3V$, $I_{O} = 1mA$ $V_{O} = 0.3V$, $I_{O} = 5mA$ $V_{O} = 0.3V$, $I_{O} = 10mA$
Output Voltage	DDC124EH DDC144EH DDC143EH DDC114YH DDC123JH DDC114EH	V _{O(on)}	_	0.1	0.3	V	I _O /I _I = 10mA / 0.5mA I _O /I _I = 10mA / 0.5mA I _O /I _I = 10mA / 0.5mA I _O /I _I = 5mA / 0.25mA I _O /I _I = 5mA / 0.25mA I _O /I _I = 10mA / 0.5mA
Input Current	DDC124EH DDC144EH DDC143EH DDC114YH DDC123JH DDC114EH	lı	_	_	0.36 0.18 1.8 0.88 3.6 0.88	mA	V _I = 5V
Output Current		$I_{O(off)}$	_	_	0.5	μΑ	$V_{CC} = 50V, V_I = 0V$
DC Current Gain	DDC124EH DDC144EH DDC143EH DDC114YH DDC123JH DDC114EH	G _l	56 68 20 68 80 30	_	_	_	V _O = 5V, I _O = 5mA V _O = 5V, I _O = 5mA V _O = 5V, I _O = 10mA V _O = 5V, I _O = 10mA V _O = 5V, I _O = 10mA V _O = 5V, I _O = 5mA
Gain-Bandwidth Product*		f _T		250		MHz	V _{CE} = 10V, I _E = 5mA, f = 100MHz

^{*} Transistor - For Reference Only



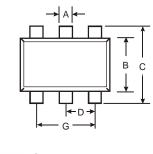
Typical Curves - DDC143EH

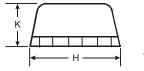




Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

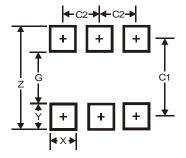




	SOT563							
Dim	Min	Max	Тур					
Α	0.15	0.30	0.20					
В	1.10	1.25	1.20					
С	1.55	1.70	1.60					
D	-	-	0.50					
G	0.90	1.10	1.00					
Н	1.50	1.70	1.60					
K	0.55	0.60	0.60					
L	0.10	0.30	0.20					
M	M 0.10 0.18 0.11							
All	Dimens	sions in	mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.2
G	1.2
Х	0.375
Y	0.5
C1	1.7
C2	0.5



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NSBC123TF3T5G NSBC143TF3T5G NSVMUN2212T1G NSVMUN5111DW1T3G NSVMUN5314DW1T3G NSVUMC2NT1G
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